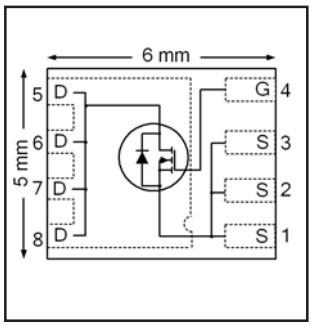
International
IOR Rectifier

IRFH7110PbF

HEXFET® Power MOSFET

V_{DS}	100	V
$V_{gs\ max}$	± 20	V
$R_{DS(on)\ max}$ ($@V_{GS}$ = 10V)	13.5	mΩ
$Q_{G\ (typical)}$	58	nC
$R_{G\ (typical)}$	0.6	Ω
I_D ($@T_{c(Bottom)}$ = 25°C)	50⑦	A



Applications

- Secondary Side Synchronous Rectification
- Inverters for DC Motors
- DC-DC Brick Applications
- Boost Converters

Features and Benefits

Features		Benefits
Low RDSon (< 13.5mW)		Lower Conduction Losses
Low Thermal Resistance to PCB (< 1.2°C/W)		Enables better thermal dissipation
Low Profile (<0.9 mm)	results in	Increased Power Density
Industry-Standard Pinout	⇒	Multi-Vendor Compatibility
Compatible with Existing Surface Mount Techniques		Easier Manufacturing
RoHS Compliant Containing no Lead, no Bromide and no Halogen		Environmentally Friendlier
MSL1, Industrial Qualification		Increased Reliability

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRFH7110TRPBF	PQFN 5mm x 6mm	Tape and Reel	4000	
IRFH7110TR2PBF	PQFN 5mm x 6mm	Tape and Reel	400	

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	100	V
V_{GS}	Gate-to-Source Voltage	± 20	
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V	11	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 10V	8.6	
I_D @ $T_{C(Bottom)}$ = 25°C	Continuous Drain Current, V_{GS} @ 10V	58⑥⑦	
I_D @ $T_{C(Bottom)}$ = 100°C	Continuous Drain Current, V_{GS} @ 10V	37⑥	
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Package Limited)	50⑦	
I_{DM}	Pulsed Drain Current ①	240	
P_D @T_A = 25°C	Power Dissipation ⑤	3.6	W
P_D @$T_{C(Bottom)}$ = 25°C	Power Dissipation ⑤	104	
	Linear Derating Factor ⑤	0.029	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Notes ① through ⑦ are on page 9

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	100	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.09	—	V/°C	Reference to 25°C, I_D = 1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	10.6	13.5	mΩ	V_{GS} = 10V, I_D = 35A ③
$V_{GS(th)}$	Gate Threshold Voltage	2.0	3.0	4.0	V	V_{DS} = V_{GS}, I_D = 100µA
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-9.0	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	µA	V_{DS} = 100V, V_{GS} = 0V
		—	—	250		V_{DS} = 100V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -20V
gfs	Forward Transconductance	74	—	—	S	V_{DS} = 25V, I_D = 35A
Q_g	Total Gate Charge	—	58	87	nC	V_{DS} = 50V V_{GS} = 10V I_D = 35A
Q_{gs1}	Pre-Vth Gate-to-Source Charge	—	11	—		
Q_{gs2}	Post-Vth Gate-to-Source Charge	—	3.6	—		
Q_{gd}	Gate-to-Drain Charge	—	16	—		
Q_{godr}	Gate Charge Overdrive	—	27.4	—		
Q_{sw}	Switch Charge (Q_{gs2} + Q_{gd})	—	19.6	—		
Q_{oss}	Output Charge	—	17	—	nC	V_{DS} = 16V, V_{GS} = 0V
R_G	Gate Resistance	—	0.6	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	V_{DD} = 50V, V_{GS} = 10V I_D = 35A R_G=1.8Ω
t_r	Rise Time	—	23	—		
$t_{d(off)}$	Turn-Off Delay Time	—	22	—		
t_f	Fall Time	—	18	—		
C_{iss}	Input Capacitance	—	3240	—	pF	V_{GS} = 0V V_{DS} = 25V f = 1.0MHz
C_{oss}	Output Capacitance	—	300	—		
C_{rss}	Reverse Transfer Capacitance	—	140	—		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	110	mJ
I_{AR}	Avalanche Current ①	—	35	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	50⑦	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	240		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	T_J = 25°C, I_S = 35A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	—	27	41	ns	T_J = 25°C, I_F = 35A, V_{DD} = 50V
Q_{rr}	Reverse Recovery Charge	—	140	210	nC	di/dt = 500A/µs ③
t_{on}	Forward Turn-On Time	Time is dominated by parasitic Inductance				

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (Bottom)	Junction-to-Case ④	—	1.2	°C/W
$R_{\theta JC}$ (Top)	Junction-to-Case ④	—	32	
$R_{\theta JA}$	Junction-to-Ambient ④⑤	—	35	
$R_{\theta JA}$ (<10s)	Junction-to-Ambient ⑤	—	22	

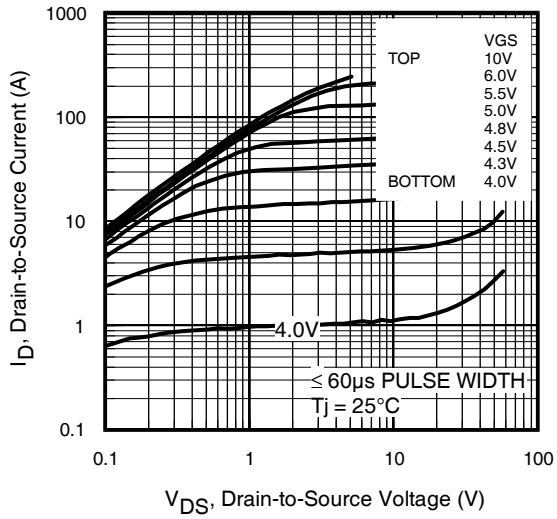


Fig 1. Typical Output Characteristics

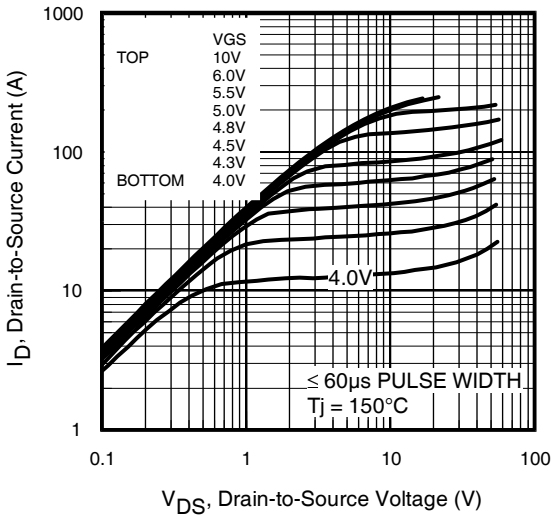


Fig 2. Typical Output Characteristics

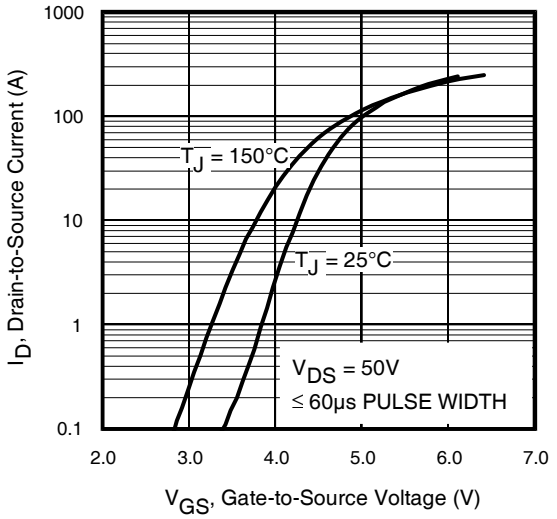


Fig 3. Typical Transfer Characteristics

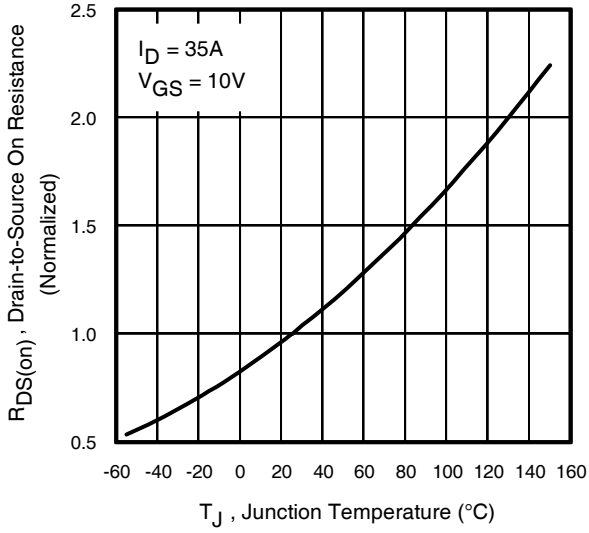


Fig 4. Normalized On-Resistance vs. Temperature

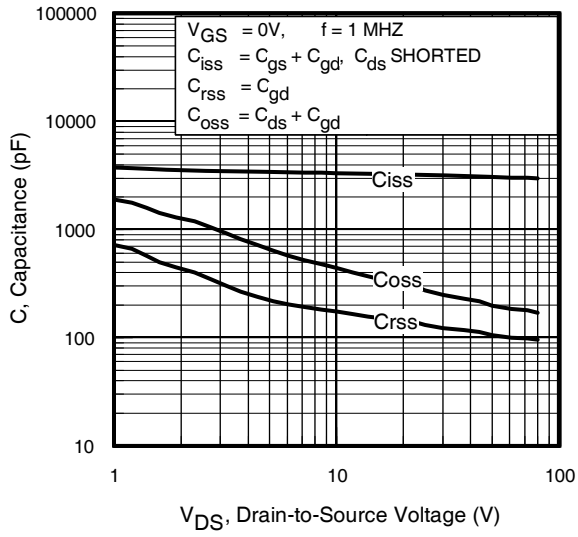


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

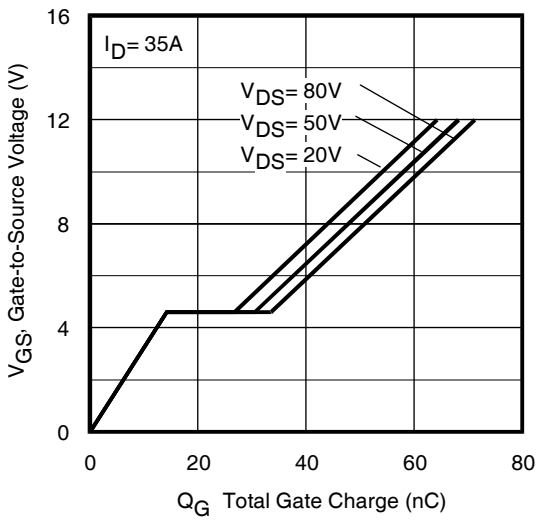


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

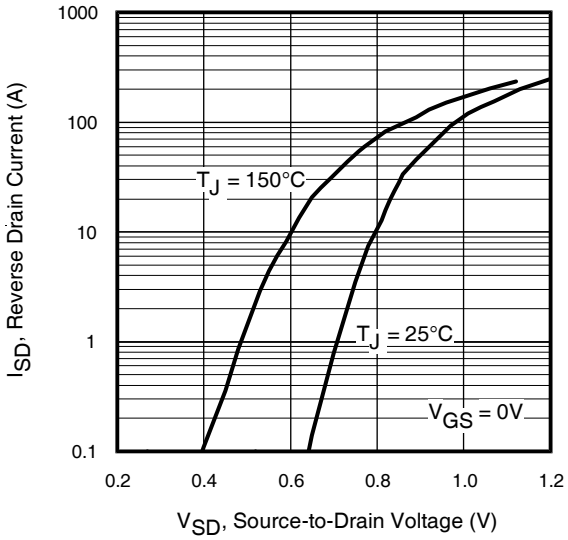


Fig 7. Typical Source-Drain Diode Forward Voltage

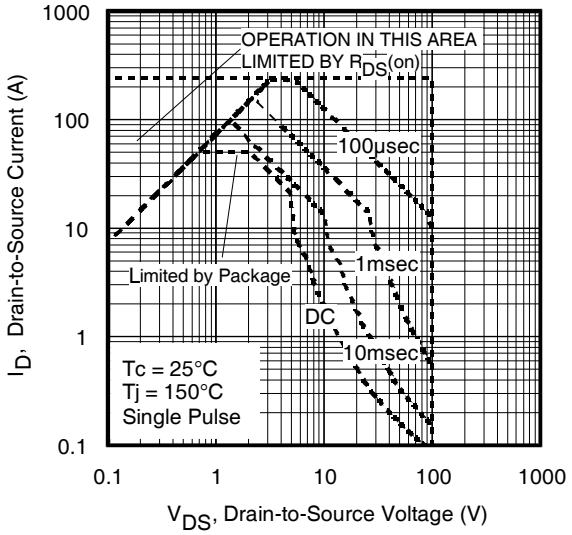


Fig 8. Maximum Safe Operating Area

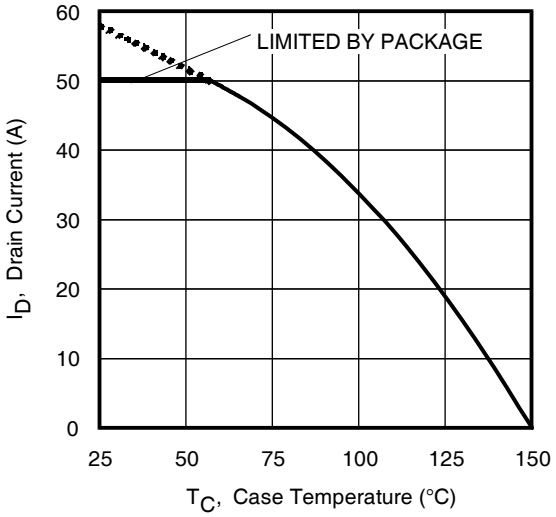


Fig 9. Maximum Drain Current vs. Case (Bottom) Temperature

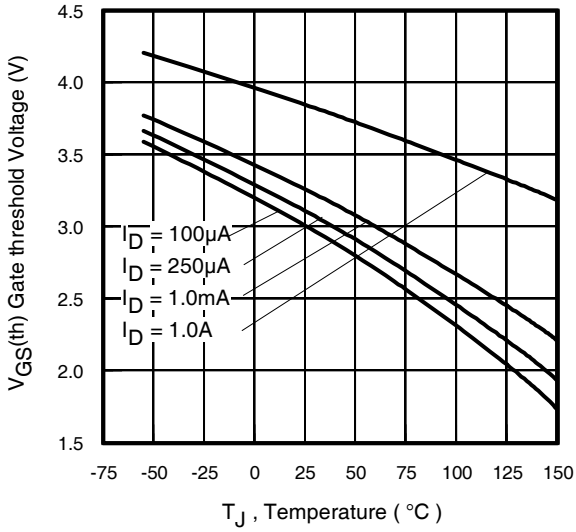


Fig 10. Threshold Voltage vs. Temperature

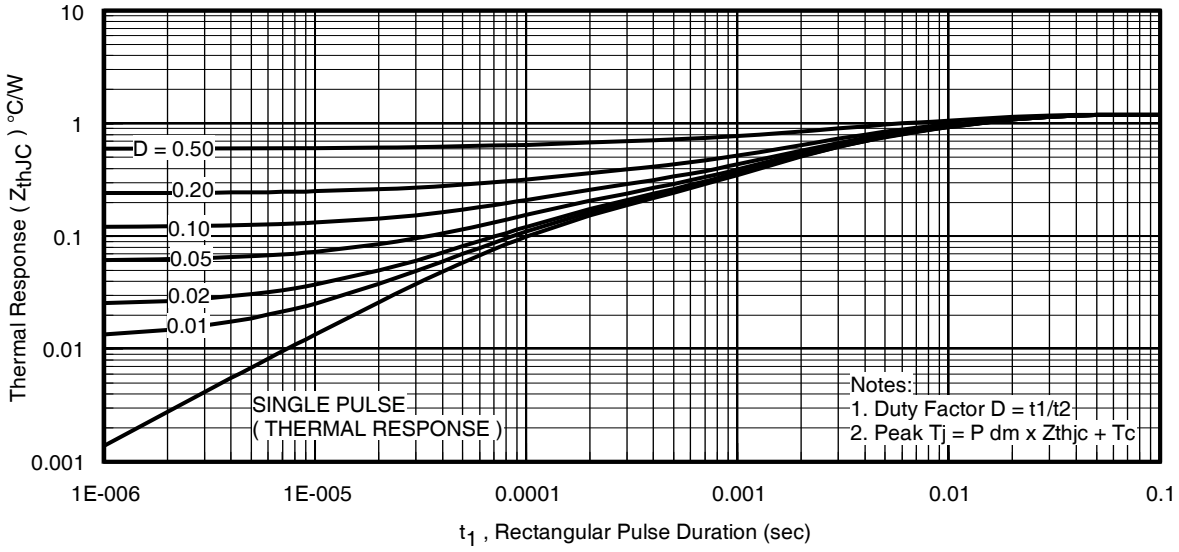


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case (Bottom)

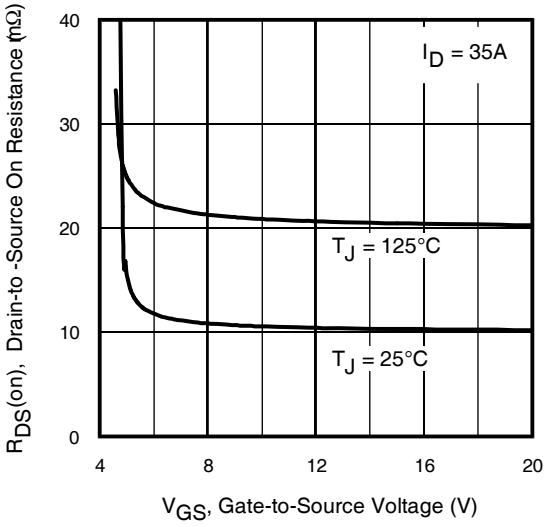


Fig 12. On-Resistance vs. Gate Voltage

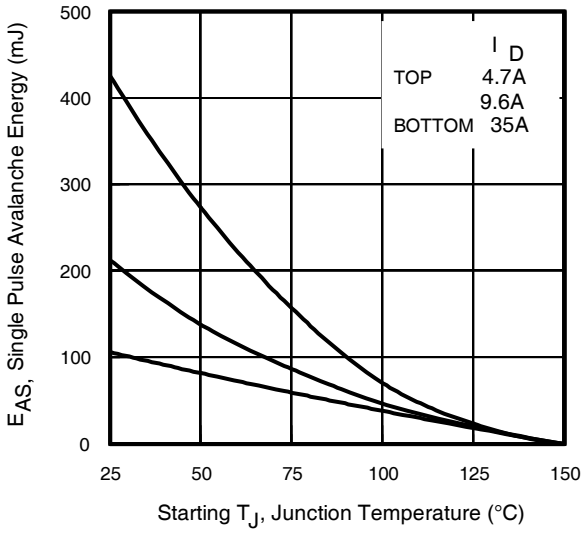


Fig 13. Maximum Avalanche Energy vs. Drain Current

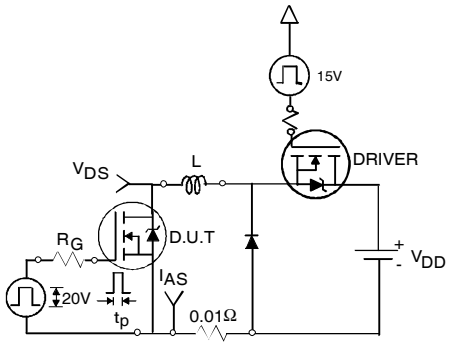


Fig 14a. Unclamped Inductive Test Circuit

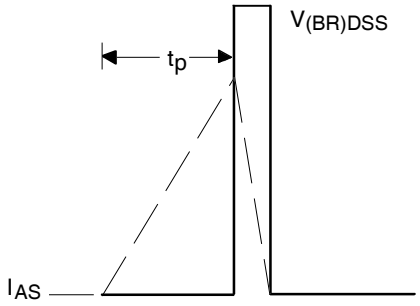


Fig 14b. Unclamped Inductive Waveforms

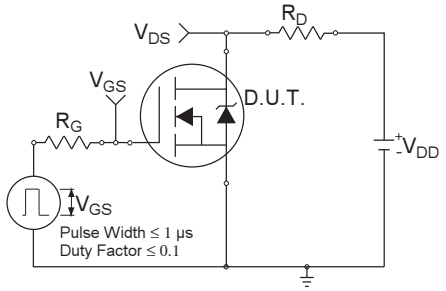


Fig 15a. Switching Time Test Circuit

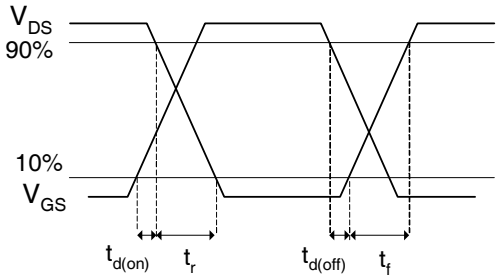


Fig 15b. Switching Time Waveforms

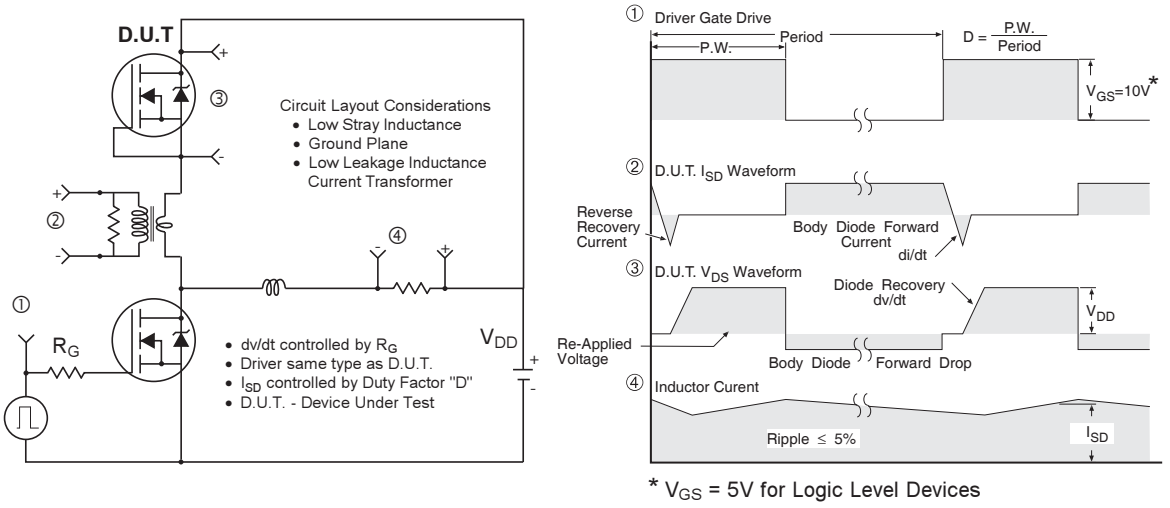


Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

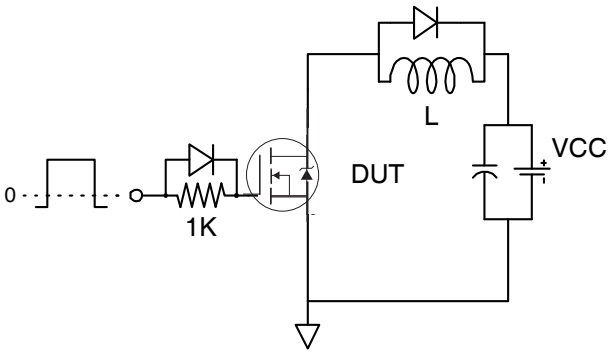


Fig 17. Gate Charge Test Circuit

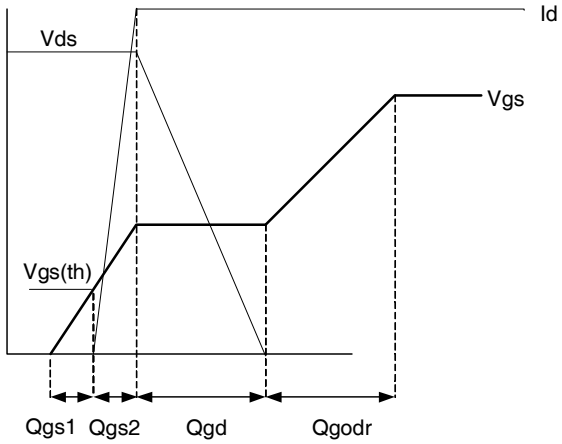
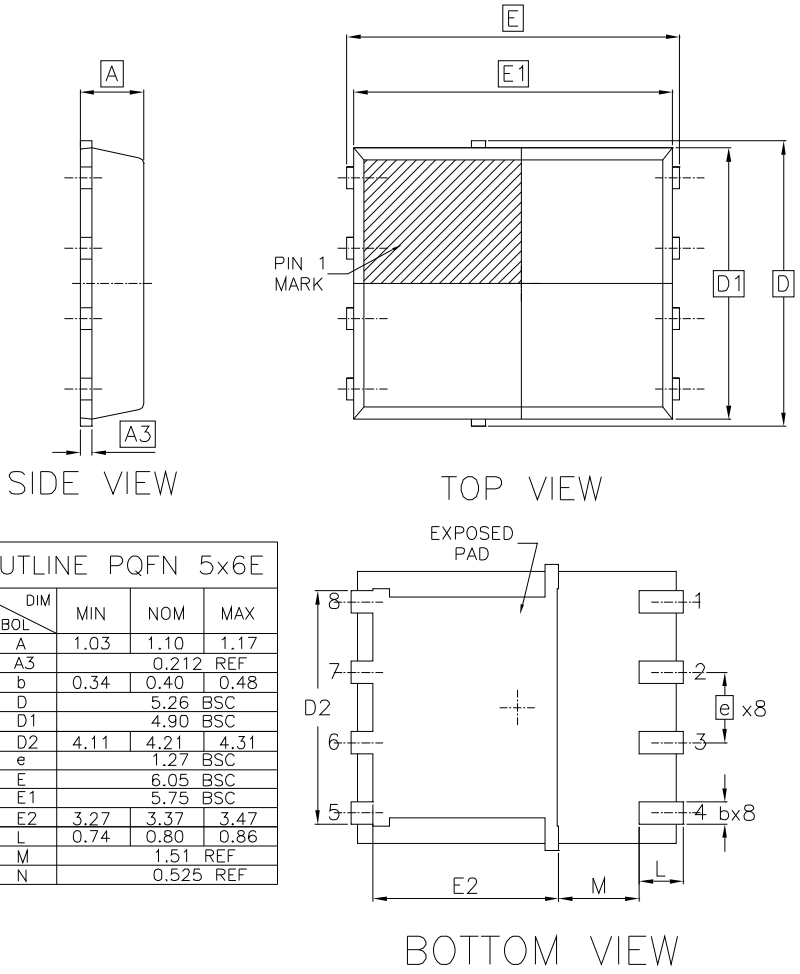


Fig 18. Gate Charge Waveform

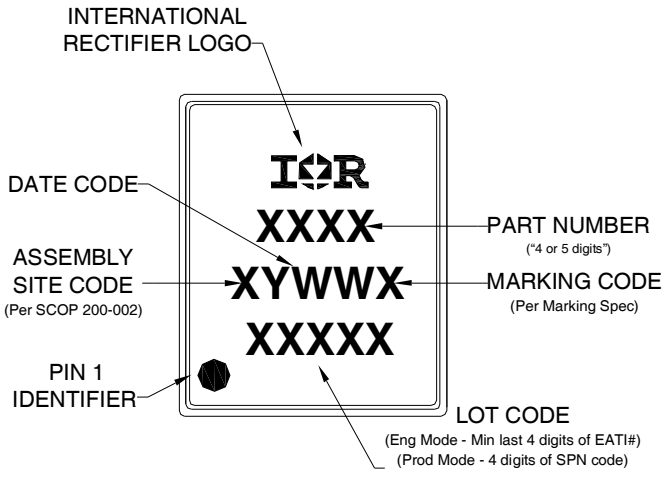
PQFN 5x6 Outline "E" Package Details



OUTLINE PQFN 5x6E			
DIM / SYMBOL	MIN	NOM	MAX
A	1.03	1.10	1.17
A3		0.212 REF	
b	0.34	0.40	0.48
D		5.26 BSC	
D1		4.90 BSC	
D2	4.11	4.21	4.31
e		1.27 BSC	
E		6.05 BSC	
E1		5.75 BSC	
E2	3.27	3.37	3.47
L	0.74	0.80	0.86
M		1.51 REF	
N		0.525 REF	

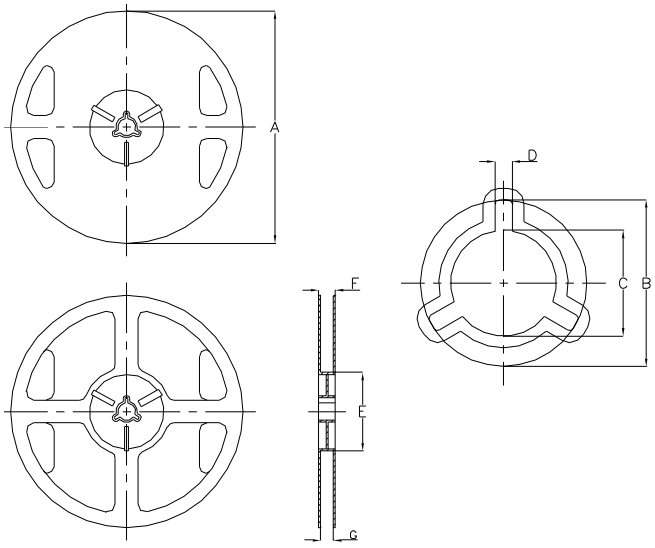
For footprint and stencil design recommendations, please refer to application note AN-1154 at http://www.irf.com/technical-info/appnotes/an-1154.pdf

PQFN 5x6 Outline "E" Part Marking



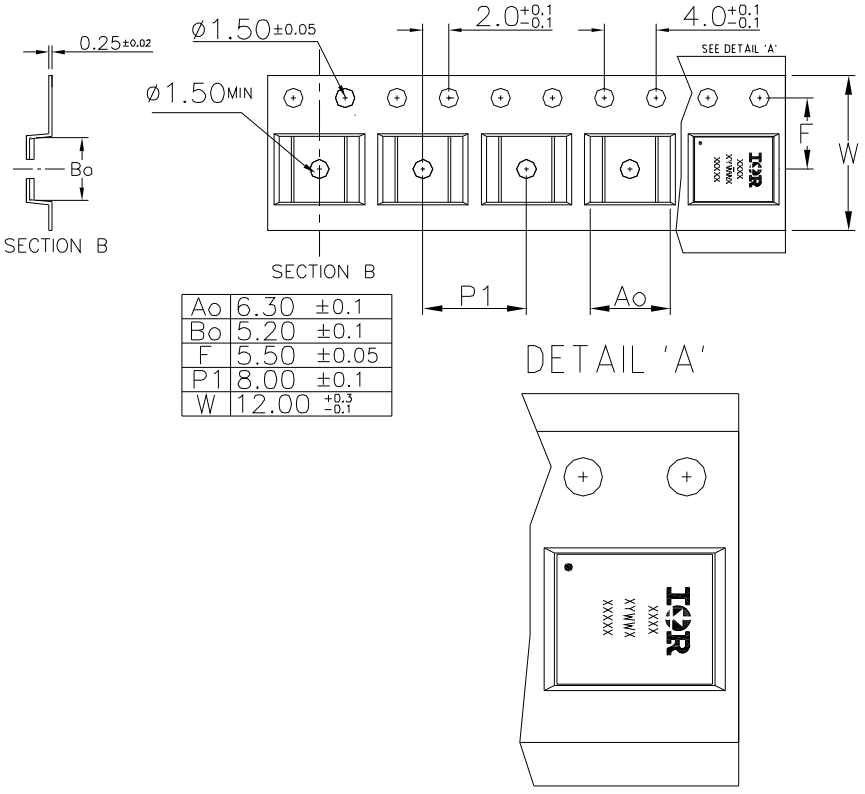
Note: For the most current drawing please refer to IR website at: http://www.irf.com/package/

PQFN 5x6 Outline "E" Tape and Reel



NOTE: Controlling dimensions in mm Std reel quantity is 4000 parts.

REEL DIMENSIONS								
STANDARD OPTION **(QTY 4000)**					TR1 OPTION **(QTY 400)**			
	METRIC		IMPERIAL		METRIC		IMPERIAL	
CODE	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX
A	329.5	330.5	12.972	13.011	177.5	178.5	6.988	7.028
B	20.9	21.5	0.823	0.846	20.9	21.5	0.823	0.846
C	12.8	13.5	0.504	0.532	13.2	13.8	0.520	0.543
D	1.7	2.3	0.067	0.091	1.9	2.3	0.075	0.091
E	97	99	3.819	3.898	65	66	2.350	2.598
F	Ref	17.4			Ref	12		
G	13	14.5	0.512	0.571	13	14.5	0.512	0.571



Qualification information†

Qualification level	Industrial†† (per JEDEC JESD47F ††† guidelines)	
Moisture Sensitivity Level	PQFN 5mm x 6mm	MSL1 (per JEDEC J-STD-020D†††)
RoHS compliant	Yes	

† Qualification standards can be found at International Rectifier's web site
http://www.irf.com/product-info/reliability

†† Higher qualification ratings may be available should the user have such requirements.
Please contact your International Rectifier sales representative for further information:
http://www.irf.com/whoto-call/salesrep/

††† Applicable version of JEDEC standard at the time of product release.

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting T_J = 25°C, L = 0.174mH, R_G = 50Ω, I_{AS} = 35A.

③ Pulse width ≤ 400µs; duty cycle ≤ 2%.

④ R_θ is measured at T_J of approximately 90°C.

⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.

⑥ Calculated continuous current based on maximum allowable junction temperature.

⑦ Package is limited to 50A by die-source to lead-frame bonding technology

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903
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